

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 2N6439** is a Common Emitter Device Designed For Large signal output amplifier stages in the 225-400 MHz range.

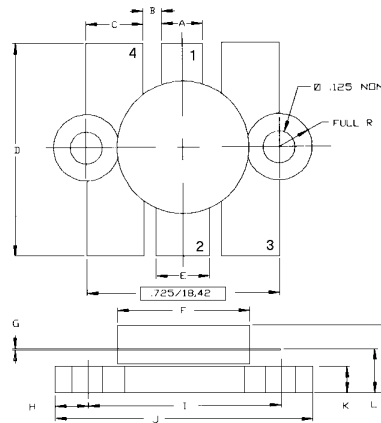
FEATURES INCLUDE:

- Internal Input Matching Network
- **30:1** Load VSWR Capability
- All Gold Metalization

MAXIMUM RATINGS

V_{CB}	60 V
P_{DISS}	146 W @ T _C = 25 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.2 °C/W

PACKAGE STYLE .500 6L FLG



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.150/.3,43	.160/.4,06
B	.045/.1,14	
C	.210/.5,33	.220/.5,59
D	.835/.2,21	.865/.2,97
E	.200/.5,08	.210/.5,33
F	.490/.12,45	.510/.12,95
G	.003/.0,08	.007/.0,18
H	.125/.3,18	
I	.720/.18,29	.730/.18,54
J	.970/.24,64	.980/.24,89
K	.095/.2,41	.105/.2,67
L	.150/.3,81	.170/.4,32
M		.280/.7,11

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 50 mA	33			V
BV_{CES}	I _C = 50 mA	60			V
BV_{CBO}	I _E = 5.0 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		100	---
C_{OB}	V _{CB} = 28 V f = 1 MHz		67	75	pF
G_{Pe}	V _{CE} = 28 V P _{OUT} = 60 W f = 225- 400 MHz	7.8	8.5		
G_{Pe}	V _{CE} = 28 V P _{OUT} = 60 W f = 400 MHz	7.8	10.0		dB
η_C		55			%
Ψ		30:1			---